

30V N-Channel Enhancement Mode MOSFET

Current

2A

Features

Voltage

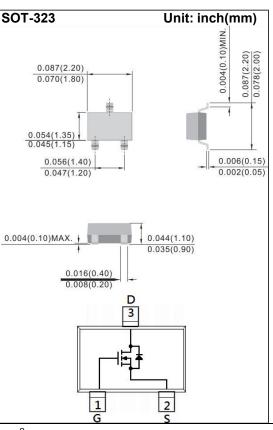
• RDS(ON), VGS@10V, ID@1.9A<70mΩ

30 V

- RDS(ON), VGS@4.5V, ID@1.6A<75mΩ
- Rds(on), Vgs@2.5V, Id@1.2A<85m Ω
- RDS(ON), VGS@1.8V, ID@0.7A<110mΩ
- Advanced Trench Process Technology

Mechanical Data

- Case: SOT-323 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00018 ounces, 0.005 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V
Continuous Drain Current		ID	2	A
Pulsed Drain Current		I _{DM}	7	А
Power Dissipation	T _a =25°C	_	350	mW
	Derate above 25°C	PD	2.8	mW/ °C
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C
Typical Thermal resistance				
Junction to Ambient (Note 3)		R _{θJA}	357	°C/W

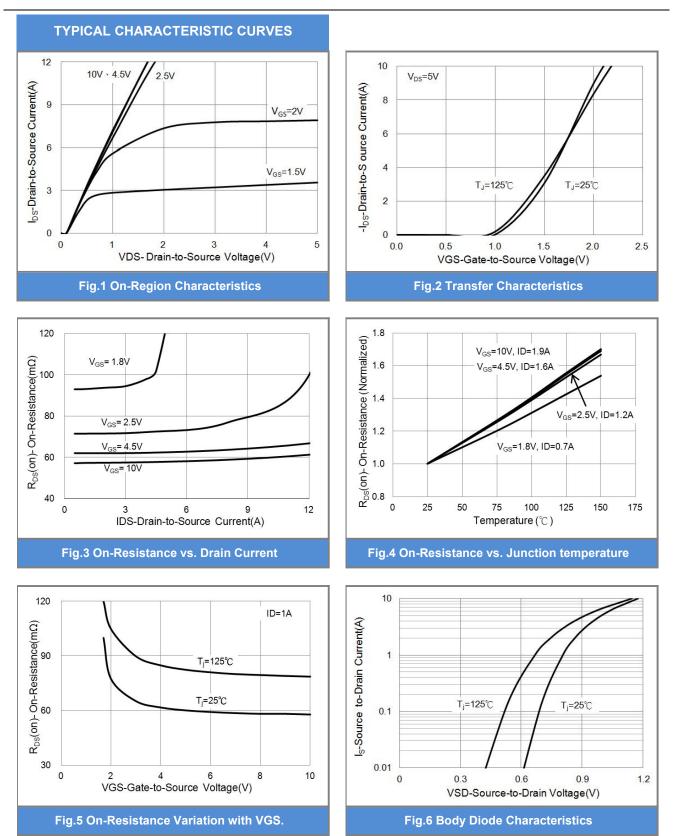


PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.4	0.72	1.2	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =1.9A	-	58	70	- mΩ
		V _{GS} =4.5V, I _D =1.6A	-	61	75	
		V _{GS} =2.5V, I _D =1.2A	-	69	85	
		V _{GS} =1.8V, I _D =0.7A	-	80	110	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	0.01	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 12V, V _{DS} =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Dynamic						
Total Gate Charge	Qg		-	4.8	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =15V, I _D =1.9A, V _{GS} =10V ^(Note 1,2)	-	0.5	-	
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	0.7	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	447	-	pF
Output Capacitance	Coss	f=1.0MHZ	-	34	-	
Reverse Transfer Capacitance	Crss		-	22	-	
Switching						
Turn-On Delay Time	td _(on)		-	2	-	- ns
Turn-On Rise Time	tr	V _{DD} =15V, I _D =1.9A, V _{GS} =10V,		38	-	
Turn-Off Delay Time	td _(off)			812	-	
Turn-Off Fall Time	tf	R _G =6Ω ^(Note 1,2)	-	64	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	0.5	A
Diode Forward Voltage	V _{SD}	I _S =1.0A, V _{GS} =0V		0.77	1.2	V

NOTES :

- 1. Pulse width300us, Duty cycle2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited







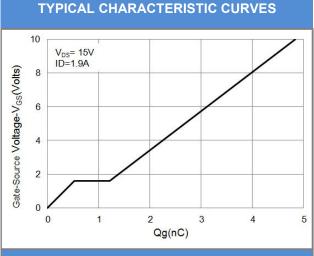


Fig.7 Gate-Charge Characteristics

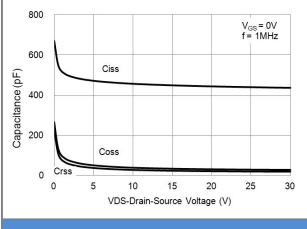
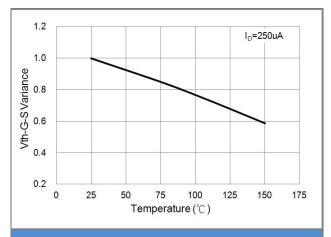


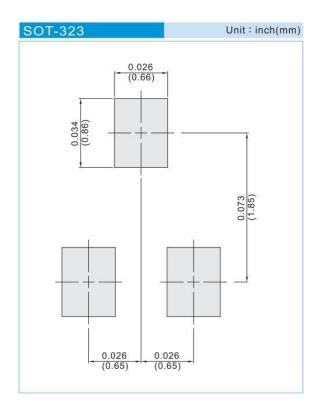
Fig.9 Capacitance vs. Drain-Source Voltage.







MOUNTING PAD LAYOUT





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